Data Sheet
(Rev. 1.0)
for S1A0071

Audio Processor for Class-D Power AMP

Digital & Analog Co., Ltd.

CONTENT

1. INTRODUCTION	3
2. BLOCK DIAGRAM	4
3 ABSOLUTE MAXIMUM RATINGS	4
4. PIN DESCRIPTION	5
5. ELECTRIC CHARATERISTICS	7
6. TYPICAL PERFORMANCE	8
7. TEST CIRCUIT	13
8. APPLICATION CIRCUIT	14
9. APPLICATION NOTE	15
10. PACKAGE DIMENSIONS	20

1. INTRODUCTION

The S1A0071 is an Audio processor for Class D-type audio amplifier, will help you to make more easier the class D type audio amplifier and sound system. This is designed by the Cool Power Processing (CPPTM) technology. The CPP have a characteristic of high fidelity and high power efficiency.

OVERVIEW

○ Sound Processing : CPPTM (Cool Power Processing) Class-D Architecture

O Audio Sound Processor : Voltage Amp, Current Amp, And Feed Back Amp

O System Support Circuit : Protection, Mute, Digital Logic

O High Speed Comparator, Logic Buffer include

◎ FEATURE

For Audio Power Amplifier

 \bigcirc Operating Voltage (Driver Supply) : $\pm 5.0 \text{V} \sim \pm 6.0 \text{V}$

○ External MOSFET Supply Voltage Range : ± 10V ~ ± 45V Usable

○ Wide Output Power Compatibility : 10W ~ 200W

 \bigcirc High Fidelity : 10W @ 4Ω, 0.01% THD+N

5W @ 8Ω, 0.008% THD+N

 \bigcirc High Efficiency : 83% @ 70W, 4Ω , THD+N < 10%, VCCP= ± 25 V

: 91% @ 40W, 8 Ω , THD+N < 10%, VCCP= \pm 25V

 \bigcirc Wide Bandwidth : 1 ~ 80KHz @ 8 Ω

O Dynamic Range: 105dB @ 100W Amp

 \bigcirc Damping Factor : more than 300

 \bigcirc Output Noise Voltage : 120 μV @ AES17, A-weighted Filter, Input Grounded

Very Low Pop Noise When Power on/off

Mute Function Without Pop Noise

Enable to Set Output Soft Clipping Level

○ Enable to Set P-MOS & N-MOS On-Time Delay Independently

O Protections: Internal Thermal Protection

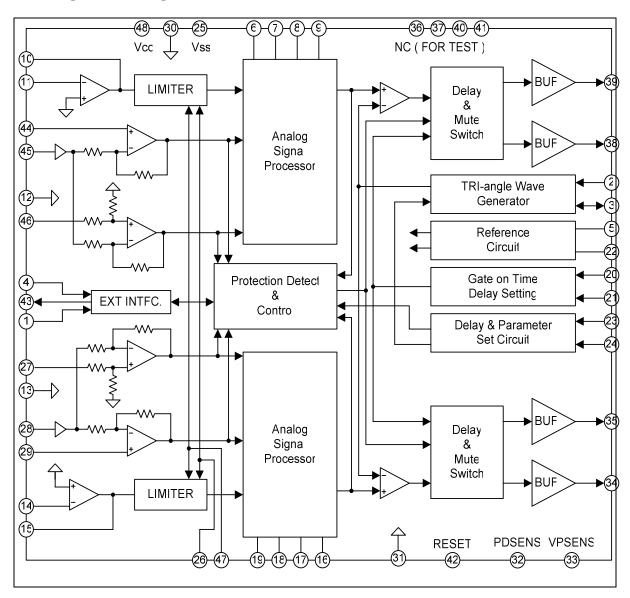
Output Over Current Protection

Output Short Protection (Output to VCCP, Output to GND, Output to VSSP)

O Protection Operating Monitor Output Pin: Direct LED Drive Enable

○ 48TSSOP Package

2. BLOCK DIAGRAM



3 ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Units
V _{CC} , V _{SS}	Driver supply voltage	± 7.5	V
Tstg	Storage Temperature	-55 to 150	°C
Topr	Operating Temperature	-25 to 75	°C
Electro-Static Discharge	Human Body Model, All pin	2000	V
	Machine Model, All pin	200	V
Electric Over Stress	All pin	16	V
Pd	Power Dissipation	1000	mW

4. PIN DESCRIPTION

NO.	Name	I/O	Description		
1	OPT	I	Active high. If it is high, PWM output is activated after power ON Mute Time, T_M . Otherwise (Default = HIGH)		
2	OSCEN	I	Triangle wave generator enable input		
3	SIO	В	Triangle wave I/O		
4	MUTE	_	Mute control input. It is also used for external protection. Active low. Low state is muted state.		
5	VD	0	Logic power supply pin (internal generated)		
6,7,8,9	CX_L	В	L-channel amp capacitor connected pin for Phase & gain		
10	VO_L	0	L-channel pre-amp output pin for gain setting		
11	VIN_L	I	L-channel pre-amp input pin		
12	GND_A	Р	L-channel sound ground		
13	GND_A	Р	R-channel sound ground		
14	VIN_R	I	R-channel pre-amp input pin		
15	VO_R	0	R-channel pre-amp output pin for gain setting		
16,17,18,19	CX_R	В	R-channel amp capacitor connected pin for Phase & gain		
20	PDCTR	I	P-MOS gate delay setting pin		
21	NDCTR	I	N-MOS gate delay setting pin		
22	VB	0	Regulated voltage output pin for internal current bias		
23	VC	-	Triangle wave magnitude setting input		
24	CDLY	_	Time delay capacitor pin for internal use		
25	VSS	Р	Negative power supply pin		
26	VLN	I	Soft clipping low level input		
27	CF2_R	I	R-channel current feed back input 2		
28	CF1_R	I	R-channel current feed back input 1		
29	VF_R	I	R-channel voltage feed back input		
30	GND_CH	Р	Control block ground		
31	GND_A	Р	Reference block ground		
32	PDSENS	I	Power Down Detection		
33	VPSENS	I	The operating voltage detection pin of the external MOSFET. When its function is not used, this pin must be tied to VCC and about 0.1uF is connected to GND		
34	NO_R	0	R-channel N-MOS switching output (PWM)		
35	PO_R	0	R-channel P-MOS switching output (PWM)		
36	NS3	-	NC (Test pin for evaluation)		
37	NS2	-	NC (Test pin for evaluation)		
38	PO_L	0	L-channel P-MOS switching output (PWM)		
39	NO_L	0	L-channel N-MOS switching output (PWM)		

	PIN DESCRIPTION (CONTINUED)					
NO.	Name	I/O	Description			
40	NS1	-	NC (Test pin for evaluation)			
41	NS0	-	- NC (Test pin for evaluation)			
42	RESET	I	I Logic reset input			
43	PMON	0	Protection monitor output			
44	VF_L	I	L-channel voltage feed back input			
45	CF2_L	I	L-channel current feed back input 2			
46	CF1_L	I	L-channel current feed back input 1			
47	VLP	I	Soft clipping high level input			
48	VCC	Р	Positive power supply pin			

^{*} I: Input, O: Output, B: Bi-directional, P: Power Supply, -: No Connection.

5. ELECTRIC CHARATERISTICS

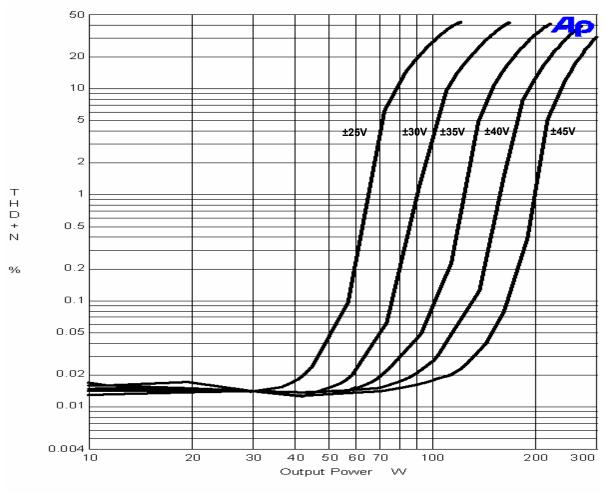
ELECTRICAL CHARACTERISTICS

Ta = 25°C, Vi = 0.3Vrms, f = 1kHz, VCC = 5V, VSS = -5V, $R_L = 4\Omega$,

Vc = 1.0V, Power Supply Voltage (VCCP, VSSP) = $\pm 30V$

Characteristic	Symbol	Condition		Unit		
			Min.	Тур.	Max.	
Supply current	Icc	Vi = 0		35		mA
Driver rising time	Tr	CL = 10pF		20		nsec
Driver falling time	Tf	CL = 10pf		20		nsec
PGATE on time delay	Tdp	CL = 10pf		20		nsec
NGATE on time delay	Tdn	CL = 10pf		20		nsec
Driver low level	Vgl	Isink = 100uA, DC	-	-4.5	-4.0	V
Driver high level	Vgh	Ipush = 100uA, DC	-1.0	-0.5	-	V
Input limiting voltage	Vlim	$V_{LP} = 1.5V, V_{LN} = -1.5V$	2.8	3.0	3.2	Vp-p
Oscillation frequency	Fosc	-	360	450	540	kHz
Oscillation level	Vosc	Vc = 1.0V	2.0	2.2	2.4	Vp-p
OSCEN conversion voltage	Vto	-	1.0	1.5	2.2	V
MUTE conversion voltage	Vtm	-	1.2	1.6	2.0	V
PMON "L" level	Vpmon	Rmon = 470Ω	-	-	0.4	V
Circuit bias voltage	Vb	-	2.8	3.0	3.2	V
Logic supply voltage	Vd	-	-1.2	-0.8	-0.2	V
Audio amp gain	Gp1	f = 1kHz.closed loop	-0.5	-2.5	-4.5	dB
	Gp2	f = 450kHz, open loop	9.0	12.0	15.0	dB
Total voltage gain	Gv	Vi = 0.1Vrms, f = 1kHz	24.0	26.0	28.0	dB
Channel balance	СВ	Vi = 0.1Vrms, f = 1kHz	-1.0	0	1.0	dB
Ripple rejection ratio	RR	Vr = 0.2Vp-p, f = 120Hz	1	-	-70	dB
Output offset voltage	Vofs	Vi = 0	1	-	0.1	>
Maximum output	Pomax1	THD = 1%, R _L = 4hm		75.2		W
	Pomax2	THD = 1%, R _L = 80hm		43.5		W
Total harmonic distortion	THD1	Po = 10W, RL = 4ohm	-	0.030		%
	THD2	Po = 50W, RL = 40hm	-	0.062		%
	THD3	Po = 5.0W, RL = 80hm	-	0.025		%
	THD4	Po = 25W ,RL = 80hm	-	0.026		%
Output noise voltage	Vno	Vi = 0 0Vrms	1	160		uVrms
Channel cross talk	СТ	Vi = 0.3Vrms	-	-	-80	dB
Mute damp ratio	Rmute	Vi = 0.8Vrms		-	-110	dB
Over current detect voltage	Voc	-	0.70	0.96	1.20	±V

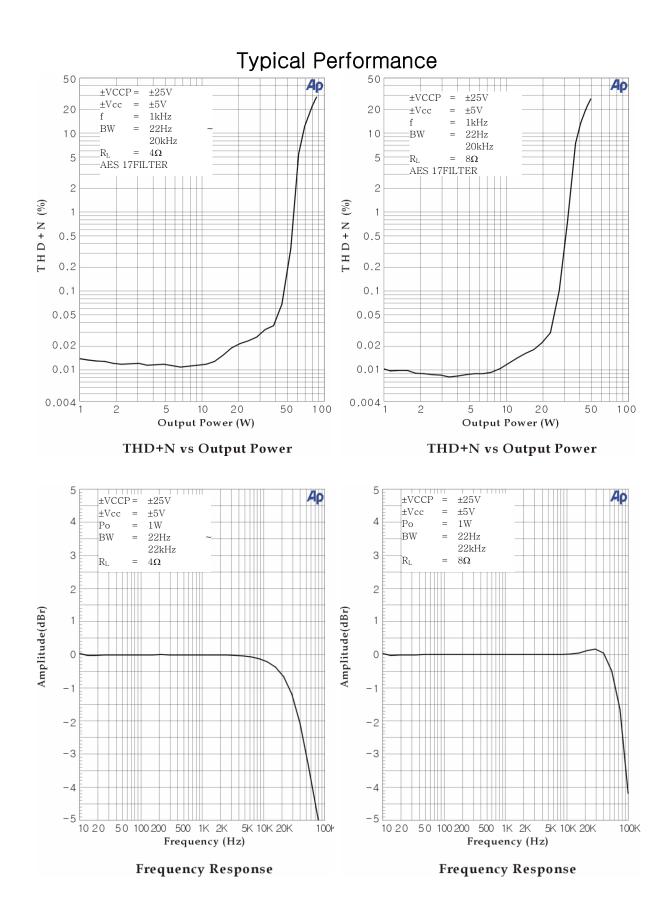
6. Typical Performance



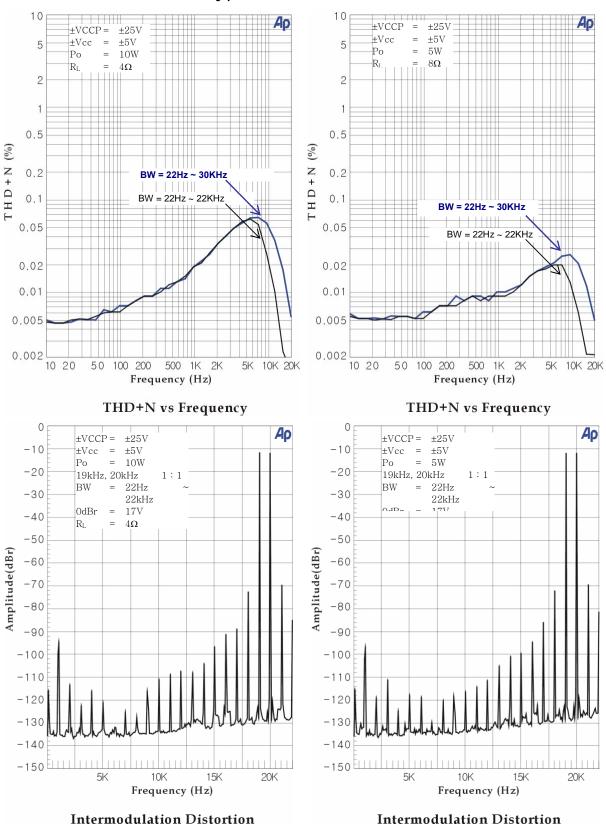
Drivers Power Supply Voltage & Out Pow

±VCCI	=	±25V	±VCCI	? =	±30V	±VCCI	=	±35V	±VCCI	=	±40V	±VCCI	=	±45V
±Vcc	=	±5V	±Vcc	=	±5V	±Vcc	=	±5V	±Vcc	=	±5V	±Vcc	=	±5V
f	=	1kHz	f	=	1kHz	f	=	1kHz	f	=	1kHz	f	=	1kHz
$_{\mathrm{BW}}$	=	22Hz~ 20kHz	$_{\mathrm{BW}}$	=	22Hz~ 20kHz	$_{\mathrm{BW}}$	=	22Hz~ 20kHz	$_{\mathrm{BW}}$	=	22Hz~ 20kHz	$_{\mathrm{BW}}$	=	22Hz~ 20kHz
R_L	=	4Ω	R_L	=	4Ω	R_L	=	4Ω	R_{L}	=	4Ω	R_{L}	=	4Ω
AES 1	7FII	LTER	AES 1	7FII	LTER	AES 1	7FII	LTER	AES 1	7FI	LTER	AES 1	7FII	LTER

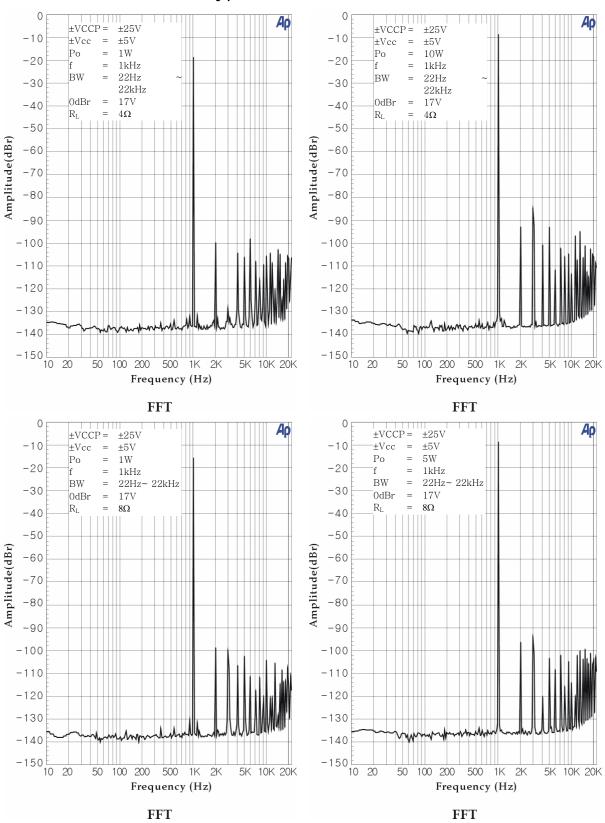
From the above measure data, the user can make an audio amplifier system with S1A0071 for several conditions. For example, if user want to make a class D type audio amplifier with specification like as 0.1% 50W system and load impedance 4Ω . User just setup the power supply and small quality of resistor and capacitor, FET drive and FET switch for this, and you can make a 0.1% 50W 2Channel as faster and easily. If you want to make a audio amplifier like as THD+N <1%, 200W 2Channel system, user can get the system quickly. Also user can make a 5.1Channel with S1A0071 3EA as easily.



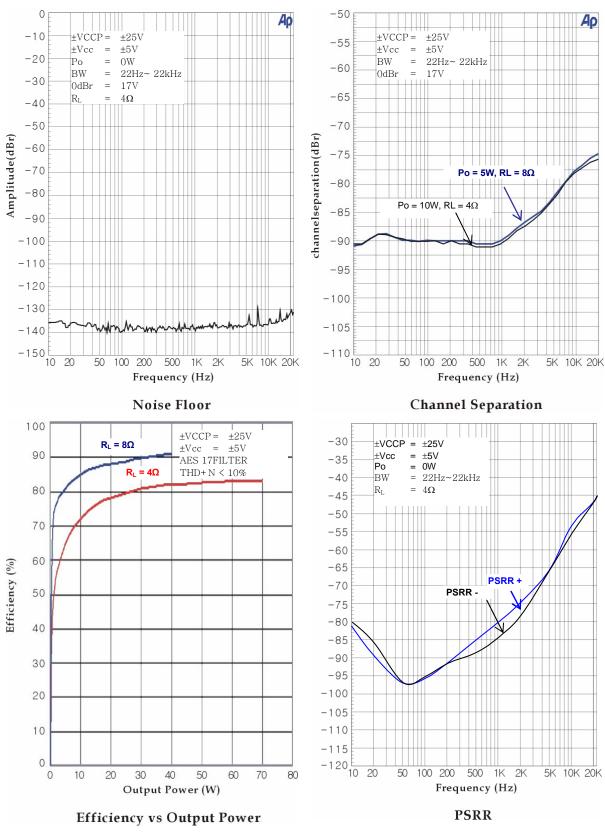
Typical Performance



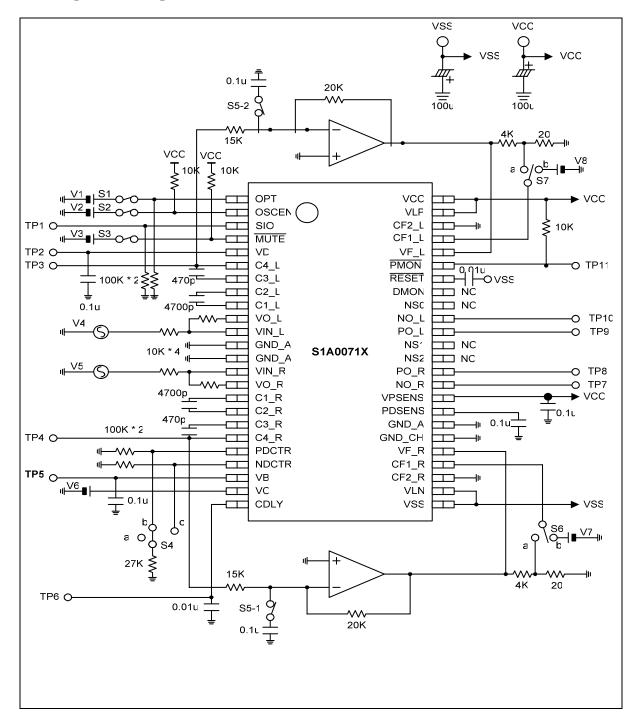
Typical Performance



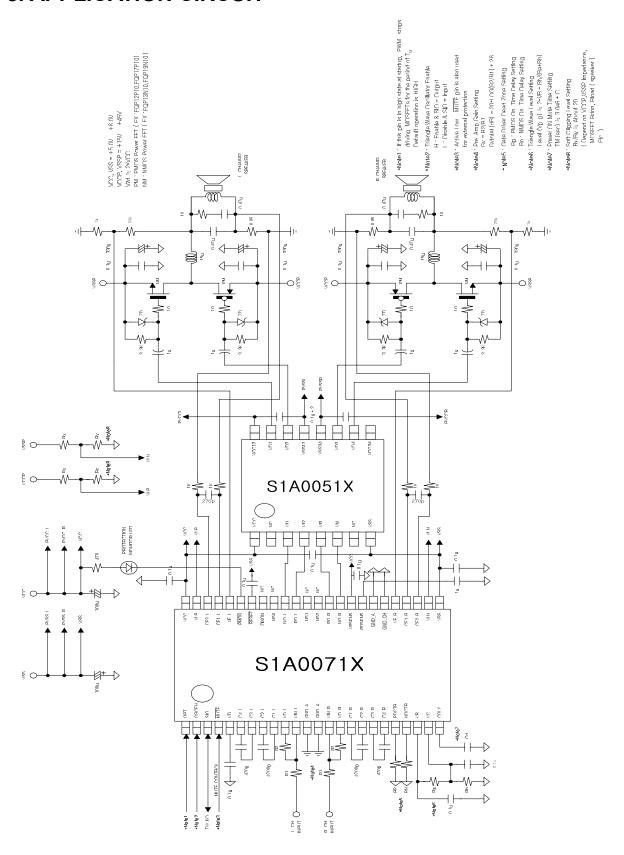
Typical Performance



7. TEST CIRCUIT



8. APPLICATION CIRCUIT



9. APPLICATION NOTE

Note 1

The OPT [Active high] controls the power on mute function [referred to Note 7]. User can prevent the unstable operation by using this pin and use can use this signal to prevent the POP noise during the power-on time.

Note 2

The OSCEN pin controls the direction of OSC pin because OSC has a bidirectional operation. The S1A0071 has a built-in triangle oscillator, so user can selectable to use the internal oscillator or external oscillator. If user wants to internal oscillator, the OSCEN pin connects to VCC then OSC is output port and used to detect the internal oscillation waveform. If user want to make an amplifier with three or more channels set, at this case, user muse be careful to make a system, specially the setting of oscillator frequency, because when user can use the each independent internal oscillators configuration, the system can be generated from mixed modulation resulting from the frequency deviation between oscillators in each chip, respectively. In such case, the oscillator in one of the IC's must be MASTER, shared with the other IC's oscillator signal, and the oscillator in the other IC's must disabled by the use of the OSCEN pin (SLAVE mode). Then, the OSCEN pin of MASTER ICs is connected to VCC (or Open) and the OSCEN pin of the other IC (Slaves) must be grounded (GND), and the SIO pins must be connected to each other. As you can see the Figure 1, the oscillator signal of the MASTER IC provides the triangle wave to the Slave ICs.

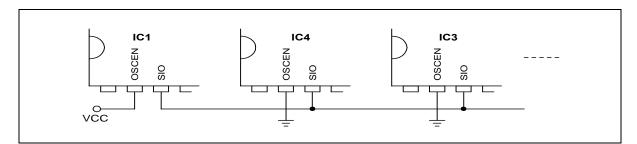


Figure 1. Multi Chip Application

Note 3

 $\overline{\text{MUTE}}$ Pin controls the switching operation of MOSFET [Active Low]. When Mute Pin is low, the PO_R, NO_R, PO_R and NO_R signal go to low level so the MOSFET operation is stop. Sound is not heard any more. This operation can be use as protection condition. So $\overline{\text{MUTE}}$ pin is also used for external protection. S1A0071 has internal protection circuit. However, if user want to add a special protection circuit to the set, the output of the added circuit which is active low is directed to the $\overline{\text{MUTE}}$ pin (PIN4), which then stops the buffer output.

Note 4

The internal gain of S1A0071 is 26dB. (Condition: R1 = R2)

When user wants to get a high gain system, User can do this by changing the values of R1 and R2. In this case, the Total Gain can be obtained as follows:

$$GAINtotal(dB) = 20 \times Log \frac{R2}{R1} + 26$$

If the values of R1 and R2 are very high, it will expect the DC offset and if the values of R1 and R2 are very low, then the THD+N value is high on high power system. By an appropriate R1 and R2 selection, you can minimize the DC offset and get the good the THD+N characteristics.

Note 5

In the application circuit, the resistor Rp connected to the PDCTR and the resistor Rn connected to NDCTR pins. User can adjust these resistors values to control the ON time delays of P-MOSFET and N-MOSFET. Because there is a turn-on delay time and rising time and falling time, turn-off delay time of each MOSFET drive, so user must set the on time delay for each P-MOSFET and N-MOSFET to prevent arm-short situation. Also more important, the Rp and Rn selection affect the sound quality and amplifier efficiency, so user should be select appropriate value.

Designed rule of S1A0071, the gate off time minimized and the ON time can be variable so that user can set the overlap time externally. The PDCTR pin and NDCTR pin voltages are generally set to that of VB (pin 22) and the flowing current, controlled by the values of Rp and Rn connected externally, can be used to delay the internal gate ON time. The recommended current range is 10Kohm to 200Kohm, from which one can select the appropriate current according to the selected output MOSFET and circuit configuration.

As the resistances increase, ON time is further delayed. Rp and Rn can set the ON time delays of P-MOSFET and N-MOSFET, respectively.

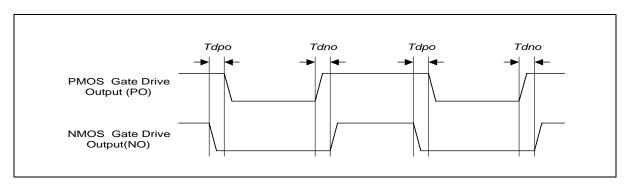
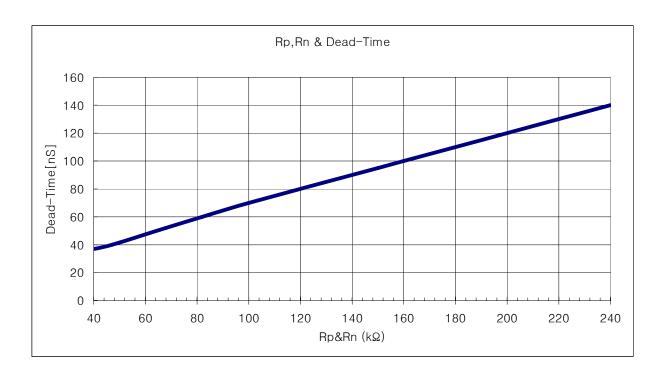


Figure 2. Gate Driver on Time Delay



Note 6

The Vc (DC Voltage of carrier frequency) sets the oscillation level of the triangle oscillator. The internal oscillation frequency is set to about 450 kHz, independent of the oscillation level, an important factor that sets the conversion gain from the internal comparator to the speaker. Based on the input Vc, the oscillation level is set to approximately \pm Vc (Vp-p), and can be monitored at the SIO (Pin3). It is acceptable to make Vc voltage from the external voltage source; however, we recommend making the Vc voltage from the regulated voltage VB (Pin22) divided by Ra and Rb. If Vc is used with the capacitor to prevent noise input, a circuit with better characteristics can be configured.

$$VC(V_{P-P}) = \frac{2 \times VB \times Rb}{(Ra + Rb)}$$
 : $V_B = 3.05V$ with VCC = 5V, VSS = -5V

To get the high THD characteristics, the gain of S1A0071 is designed as 26dB and the application circuit use the \pm 30V for main power and the 0.8V for Vc. The ratio of main power divide Vc relate a amplifier gain, so if user want to get the high power and increase the main power, then user must re-setup the Vc values. We recommended as below value for user's application.

VCCP, VSSP	± 20V	± 30V	± 45V
Ra	22K Ω	22K Ω	22K Ω
Rb	5.6K Ω	8.2K Ω	15K Ω

Note 7

When power is turned on, the circuit operates unstably, possibly generating noise. To prevent this unstable situation, the S1A0071 use the CDLY pin (pin# 24), which can be connected to a capacitor. This CDLY pin used to generate a slight time delay from power up to when the circuit starts to operate normally. The CDLY pin drive's capacity is about 1.0 μ A and the mute mode sustains until the externally connected capacitor charges to a voltage equal about VB (pin 22). The time delay can be calculated as follows:

$$Tdly(sec) = \frac{VC \times C}{I} + Ta = \frac{3 \times C}{1.0 \mu} + Ta \cong 3.0E6 \times C$$
 (Ta « Tdly)

 T_a is the internal processing time that used in the removal of circuit settling time and other pop noises. Tdly also decides the protection restart time. Among the protection functions in S1A0071, those that remove "causes" (Thermal Protection, Over Current Protection) oscillate from normal operation \rightarrow protection \rightarrow normal operation \rightarrow protection \rightarrow ..., generating very fast blocking oscillation. The Tdly decides (delays) the repeat cycle of the oscillation, which protects the circuit and controls unstable operations. Those protection functions (Output DC Short) that do not remove "causes" are not affected by Tdly, and once the cause has been removed, they return to normal operation.

Note 8

S1A0071 has a built-in limiting block at the input stage that remove noise signal that may be generated by discontinuous feedback and also this limit block operate as a clipping circuit due to over-input signal. When a specific voltage (± Vls) is applied to VLP and VLN, the soft clipping function starts to operate on the input whose value lie outside the ± Vls range, on the basis of the Pre Amp output with its gain set by R1 and R2. As a result, the entire circuit is enabled to drive only the signals that lie within the operating range, thus maintaining a continuous feedback loop which allows the circuit to output a soft clipped output waveform even for an input lying outside the output dynamic range.

VIs must be set differently according to the MOSFET power supply voltage and power supply impedance, and MOSFET ON resistance. If we assume that the power supply impedance is ideal (= 0) and MOSFET ON resistor is ideal (0 Ohm), the appropriate values for VIs values on the power supply voltage (VCCP, VSSP) would be as follows:

VCCP, VSSP	± 20V	± 30V	± 45V
VIs	± 1.05V	± 1.43V	± 2.15V

(This value is obtained by dividing MOSFET power supply voltage with Rx and Ry. Considering the speaker load resistance and power supply impedance, VIs (soft clipping level) is generated. So, VLN/VLP accepts this value, and then stable operation is expected.)

To decide on the actually appropriate VIs, you must monitor the output waveform at the set connected to the power supply. You can set Rx and Ry to values that will make VLP and VLN generate maximum waveforms, respectively; within the range that has no clipping distortion and other noises. If you don't want to operate the soft clipping function, connect VLN and VLP pins to VCC and VSS.

Other Application information

◆ PROTECTION

S1A0071 has built-in Output DC Short Protection, and Over Current Protection. When the protection block output pins are shorted to VCCP or GND or VSSP, respectively, the internal detect circuit immediately stops the buffer output.

The Over Current Detect function is driven by the Current Sensing resistor (50m), which indicates an over current if the resistor develops a potential of about 1.0V. Then the current is about 1.0(V) / 0.05 () = 20 (A). If the speaker "-" pin becomes VCCP or VSSP and DC shorted, the sensing resistor will be destroyed as well as S1A0071. To prevent IC destruction, you can insert resistors of few k in series at the CF1 pins (Pin28, 45). (Please refer to Note 5 for more details on protection return time)

◆ FET DRIVER

S1A0071 produces an output of 4.5Vp-p and low level is VSS. Any GATE BUFFER ICs can satisfy these conditions, but they should be designed as FAIR to optimally use with S1A0051, a MOSFET DRIVER

10. PACKAGE DIMENSIONS

